Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

Applications

Band switching in VHF-tuners

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

T_j=25℃

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	35	V
Forward current		I_F	100	mA
Junction temperature		T_j	150	℃
Storage temperature range		T_{stg}	-55…+150	℃

Maximum Thermal Resistance

T_j=25℃

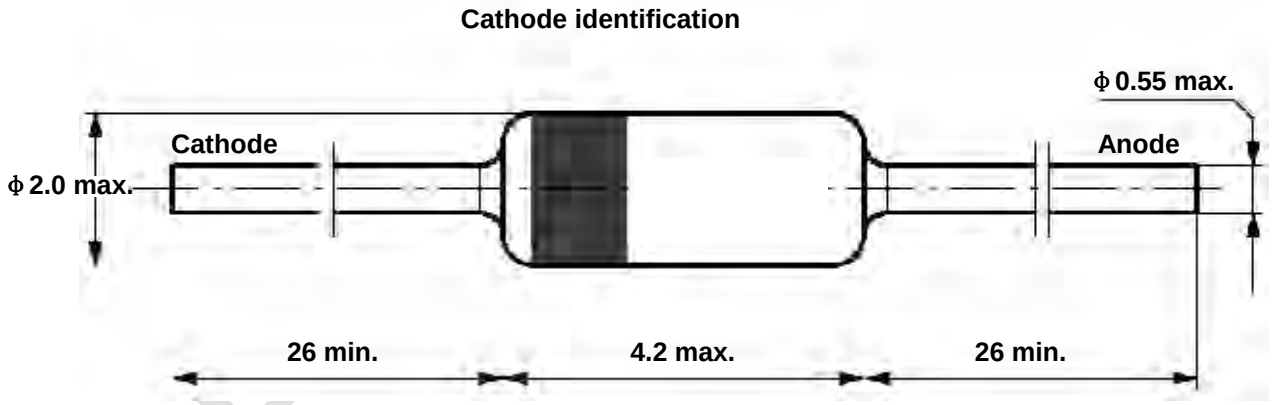
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	I=4mm, T_L=constant	R_{thJA}	350	K/W

Electrical Characteristics

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=100mA		V_F			1	V
Reverse current	V_R=20V		I_R			50	nA
Diode capacitance	f=100MHz, V_R=1V		C_D			1.5	pF
	f=100MHz, V_R=3V	BA282	C_D			1.25	pF
		BA283	C_D			1.2	pF
Differential forward resistance	f=200MHz, I_F=3mA	BA282	r_f			0.7	
		BA283	r_f			1.2	
	f=200MHz,I_F=10mA	BA282	r_f			0.5	
		BA283	r_f			0.9	
Reverse impedance	f=100MHz,V_R=1V		z_r	100			K

Dimensions in mm



Standard Glass Case
JEDEC DO 35